

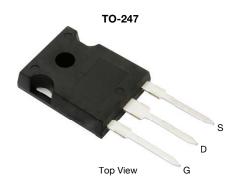
Vishay Siliconix

COMPLIANT

HALOGEN

FREE

N-Channel 150 V (D-S) 175 °C MOSFET



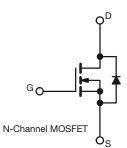
PRODUCT SUMMARY			
V _{DS} (V)	150		
$R_{DS(on)}$ max. (Ω) at $V_{GS} = 10 \text{ V}$	0.0054		
$R_{DS(on)}$ max. (Ω) at $V_{GS} = 7.5 \text{ V}$	0.0060		
Q _g typ. (nC)	110		
I _D (A)	100 d		
Configuration	Single		

FEATURES

- ThunderFET® power MOSFET
- Low R_{DS} Q_g figure-of-merit (FOM)
- Maximum 175 °C junction temperature
- 100 % R_a and UIS tested
- Material categorization: for definitions of compliance please see www.vishav.com/doc?99912

APPLICATIONS

- Synchronous rectification
- · Power supplies
- DC/AC inverter
- DC/DC converter
- · Solar micro inverter
- · Motor drive switch



ORDERING INFORMATION	
Package	TO-247
Lead (Pb)-free and halogen-free	SUG80050E-GE3

PARAMETER		SYMBOL	LIMIT	UNIT
Drain-source voltage		V_{DS}	150	
Gate-source voltage		V_{GS}	± 20	V
Continuous dunin automat	T _C = 25 °C		100 ^d	
Continuous drain current	T _C = 125 °C	l _D	100 ^d	
Pulsed drain current (t = 100 μs)		I _{DM}	300	A
Continuous source-drain diode current		I _S	100 ^d	
Single pulse avalanche current ^a	. 0.4	I _{AS}	100	
Single pulse avalanche energy ^a	L = 0.1 mH	E _{AS}	500	mJ
Maximum power dissipation $ T_{C} = 25 ^{\circ}\text{C} $ $ T_{C} = 125 ^{\circ}\text{C} $		5	500 b	10/
		P _D	167 ^b	W
Operating junction and storage temperature range		T _J , T _{stg}	-55 to +175	90
Soldering recommendations (peak temperature) c			260	°C

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	MAXIMUM	UNIT
Maximum junction-to-ambient (PCB mount) °		R _{thJA}	40	°C/W
Maximum junction-to-case (drain)	Steady state	R _{thJC}	0.3]

- a. Duty cycle ≤ 1 %
- b. See SOA curve for voltage derating
- c. When mounted on 1" square PCB (FR4 material)
- d. Package limited



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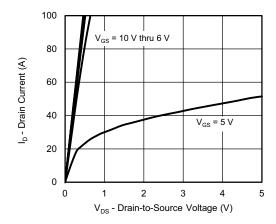
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static						
Drain-source breakdown voltage	V_{DS}	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	150	-	-	V
Gate-source threshold voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	2	-	4	V
Gate-source leakage	I_{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$	-	-	250	nA
		$V_{DS} = 150 \text{ V}, V_{GS} = 0 \text{ V}$	-	-	1	μA
Zero gate voltage drain current	I_{DSS}	$V_{DS} = 150 \text{ V}, V_{GS} = 0 \text{ V}, T_J = 125 ^{\circ}\text{C}$	-	-	150	μΑ
		V_{DS} = 150 V, V_{GS} = 0 V, T_J = 175 °C	-	-	5	mA
On-state drain current ^a	I _{D(on)}	$V_{DS} \ge 10 \text{ V}, V_{GS} = 10 \text{ V}$	30	-	-	Α
Drain-source on-state resistance a	D	$V_{GS} = 10 \text{ V}, I_D = 20 \text{ A}$	-	0.0045	0.0054	Ω
Dialii-Source oii-state resistance "	R _{DS(on)}	$V_{GS} = 7.5 \text{ V}, I_D = 15 \text{ A}$	-	0.0050	0.0063] 52
Forward transconductance ^a	9 _{fs}	$V_{DS} = 15 \text{ V}, I_D = 20 \text{ A}$	-	60	-	S
Dynamic ^b						
Input capacitance	C _{iss}		-	6250	-	pF
Output capacitance	C _{oss}	$V_{DS} = 75 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$	-	1100	-	
Reverse transfer capacitance	C _{rss}		-	65	-	
Total gate charge	Qg		-	110	165	
Gate-source charge	Q_{gs}	$V_{DS} = 75 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 20 \text{ A}$	-	33	-	nC
Gate-drain charge	Q _{gd}		-	28	-	
Gate resistance	Rg	f = 1 MHz	0.6	3.1	6.2	Ω
Turn-on delay time	t _{d(on)}		-	18	27	
Rise time	t _r	$V_{DD} = 75 \text{ V}, \text{ R}_{L} = 5 \Omega, \text{ I}_{D} \cong 15 \text{ A},$	-	44	66	no
Turn-off delay time	t _{d(off)}	V_{GEN} = 10 V, R_g = 1 Ω	-	72	108	ns
Fall time	t _f		-	55	83	
Drain-Source Body Diode Characteristi	cs					
Pulse diode forward current (t = 100 μs)	I _{SM}		-	-	100	Α
Body diode voltage	V _{SD}	I _F = 15 A, V _{GS} = 0 V	-	0.85	1.5	V
Body diode reverse recovery time	t _{rr}		-	130	195	ns
Body diode reverse recovery charge	Q _{rr}	Q _{rr} 1. 15 A 41/44 100 A / 3		0.71	1.07	μC
Reverse recovery fall time	t _a	I _F = 15 A, dl/dt = 100 A/μs	-	97	-	
Reverse recovery rise time	t _b		-	33	-	ns
Body diode peak reverse recovery charge	I _{RM(REC)}		-	12	18	Α

Notes

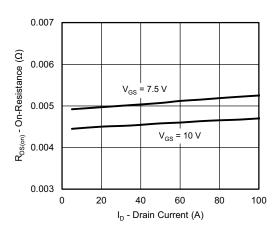
- a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%$
- b. Guaranteed by design, not subject to production testing
- c. Independent of operating temperature

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

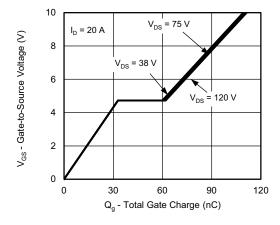




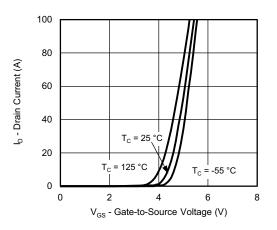
Output Characteristics



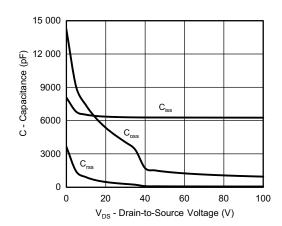
On-Resistance vs. Drain Current and Gate Voltage



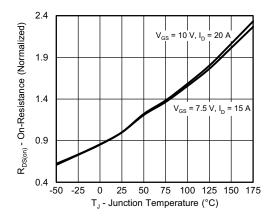
Gate Charge



Transfer Characteristics

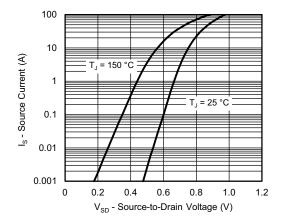


Capacitance

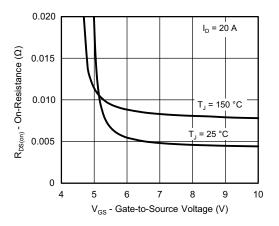


On-Resistance vs. Junction Temperature

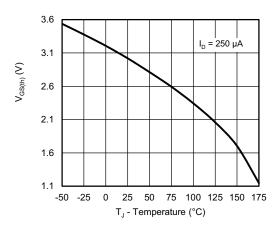




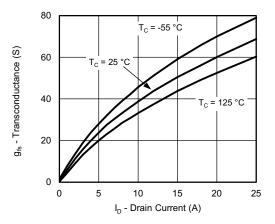
Source-Drain Diode Forward Voltage



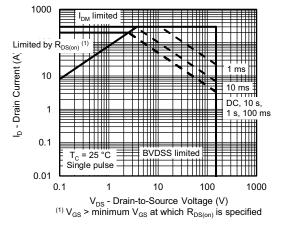
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage

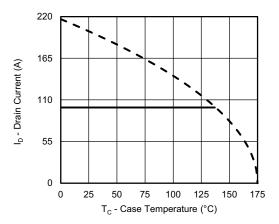


Transconductance

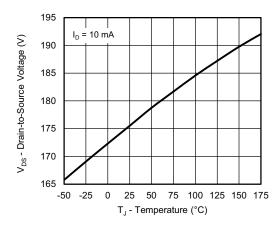


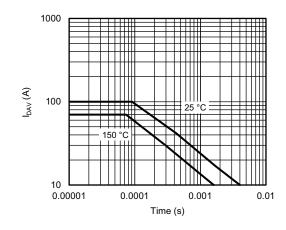
Safe Operating Area, Junction-to-Ambient





Current Derating a





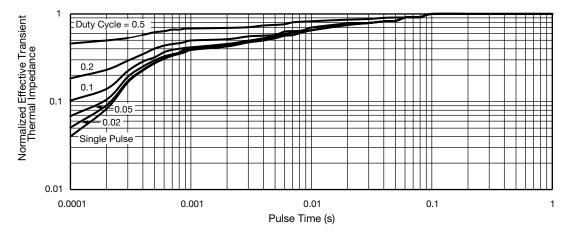
Drain Source Breakdown vs. Junction Temperature

 I_{DAV} vs. Time

Note

a. The power dissipation P_D is based on T_J max. = 25 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.





Normalized Thermal Transient Impedance, Junction-to-Case

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?75186.



TO-247AC (High Voltage)

VERSION 1: FACILITY CODE = 9







Section C--C,D-D,E-E

	MILLIMETERS			
DIM.	MIN.	NOM.	MAX.	NOTES
Α	4.83	5.02	5.21	
A1	2.29	2.41	2.55	
A2	1.17	1.27	1.37	
b	1.12	1.20	1.33	
b1	1.12	1.20	1.28	
b2	1.91	2.00	2.39	6
b3	1.91	2.00	2.34	
b4	2.87	3.00	3.22	6, 8
b5	2.87	3.00	3.18	
С	0.40	0.50	0.60	6
c1	0.40	0.50	0.56	
D	20.40	20.55	20.70	4

	MILLIMETERS			
DIM.	MIN.	NOM.	MAX.	NOTES
D1	16.46	16.76	17.06	5
D2	0.56	0.66	0.76	
Е	15.50	15.70	15.87	4
E1	13.46	14.02	14.16	5
E2	4.52	4.91	5.49	3
е		5.46 BSC		
L	14.90	15.15	15.40	
L1	3.96	4.06	4.16	6
ØΡ	3.56	3.61	3.65	7
Ø P1	7.19 ref.			
Q	5.31	5.50	5.69	
S		5.51 BSC		

- (1) Package reference: JEDEC® TO247, variation AC
- (2) All dimensions are in mm
- (3) Slot required, notch may be rounded
- (4) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm per side. These dimensions are measured at the outermost extremes of the plastic body
- (5) Thermal pad contour optional with dimensions D1 and E1
- (6) Lead finish uncontrolled in L1
- $^{(7)}$ Ø P to have a maximum draft angle of 1.5° to the top of the part with a maximum hole diameter of 3.91 mm
- (8) Dimension b2 and b4 does not include dambar protrusion. Allowable dambar protrusion shall be 0.1 mm total in excess of b2 and b4 dimension at maximum material condition



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VERSION 2: FACILITY CODE = Y



	MILLIM		
DIM.	MIN.	MAX.	NOTES
Α	4.58	5.31	
A1	2.21	2.59	
A2	1.17	2.49	
b	0.99	1.40	
b1	0.99	1.35	
b2	1.53	2.39	
b3	1.65	2.37	
b4	2.42	3.43	
b5	2.59	3.38	
С	0.38	0.86	
c1	0.38	0.76	
D	19.71	20.82	
D1	13.08	-	

	MILLIN		
DIM.	MIN.	MAX.	NOTES
D2	0.51	1.30	
Е	15.29	15.87	
E1	13.72	-	
е	5.46	BSC	
Øk	0.2	254	
L	14.20	16.25	
L1	3.71	4.29	
ØР	3.51	3.66	
Ø P1	-	7.39	
Q	5.31	5.69	
R	4.52	5.49	
S	5.51 BSC		

- (1) Dimensioning and tolerancing per ASME Y14.5M-1994
- (2) Contour of slot optional
- (3) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (4) Thermal pad contour optional with dimensions D1 and E1
- (5) Lead finish uncontrolled in L1
- (6) Ø P to have a maximum draft angle of 1.5 to the top of the part with a maximum hole diameter of 3.91 mm (0.154")
- (7) Outline conforms to JEDEC outline TO-247 with exception of dimension c



VERSION 3: FACILITY CODE = N



	MILLIMETERS		
DIM.	MIN.	MAX.	
Α	4.65	5.31	
A1	2.21	2.59	
A2	1.17	1.37	
b	0.99	1.40	
b1	0.99	1.35	
b2	1.65	2.39	
b3	1.65	2.34	
b4	2.59	3.43	
b5	2.59	3.38	
С	0.38	0.89	
c1	0.38	0.84	
D	19.71	20.70	
D1	13.08	-	

	MILLIM	IETERS
DIM.	MIN.	MAX.
D2	0.51	1.35
E	15.29	15.87
E1	13.46	-
е	5.46	BSC
k	0.254	
L	14.20	16.10
L1	3.71	4.29
N	7.62	BSC
Р	3.56	3.66
P1	-	7.39
Q	5.31	5.69
R	4.52	5.49
S	5.51	BSC

ECN: E22-0452-Rev. G, 31-Oct-2022

DWG: 5971

- ⁽¹⁾ Dimensioning and tolerancing per ASME Y14.5M-1994
- (2) Contour of slot optional
- (3) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (4) Thermal pad contour optional with dimensions D1 and E1
- (5) Lead finish uncontrolled in L1
- (6) Ø P to have a maximum draft angle of 1.5 to the top of the part with a maximum hole diameter of 3.91 mm (0.154")



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